



Pin Description

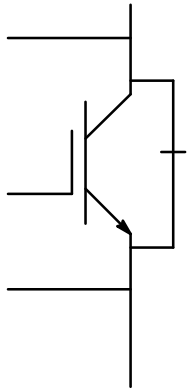


Figure 1. Pin Description

VE-Trac™ Direct Module NVH820S75L4SPC

MODULE CHARACTERISTICS (T_{vj} = 25°C, Unless Otherwise Specified)

Symbol	Parameter	Rating	Unit
T _{vj}	Operating Junction Temperature	-40 to 175	°C
T _{STG}	Storage Temperature	-40 to 125	°C
V _{ISO}	Isolation Voltage (DC, 0 Hz, 1 s)	4200	V
L _{sCE}	Stray Inductance	8	nH
RCC'+EE'	Module Lead Resistance, Terminals – Chip	0.75	mΩ
G			

VE-Trac™ Direct Module NVH820S75L4SPC



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CHARACTERISTICS OF INVERSE DIODE ($T_{vj} = 25^{\circ}\text{C}$, Unless Otherwise Specified)

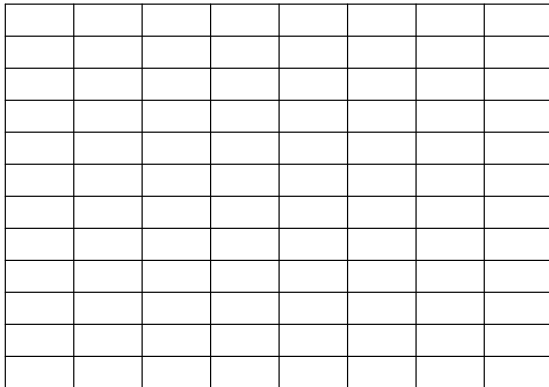
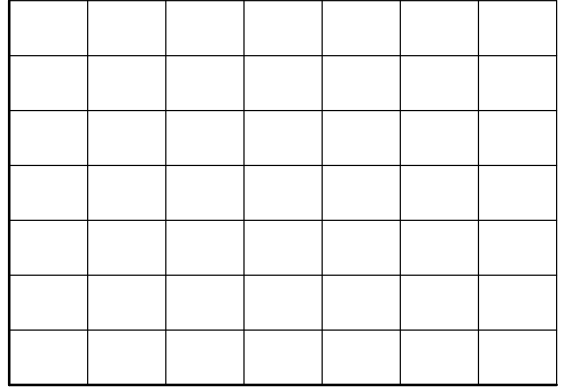
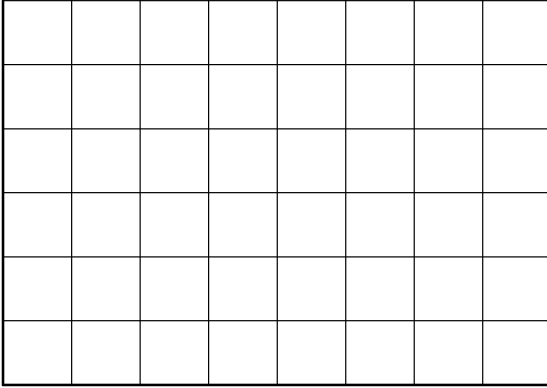
Symbol	Parameters	Conditions		Min	Typ	Max	Unit
V_F	Diode Forward Voltage (Terminal)	$I_F = 600 \text{ A}$	$T_{vj} = 25^{\circ}\text{C}$	–	1.70	1.95	V
	Diode Forward Voltage (Chip)	$I_F = 600 \text{ A}$	$T_{vj} = 25^{\circ}\text{C}$	–	1.60	1.85	
			$T_{vj} = 150^{\circ}\text{C}$	–	1.55	–	
		$I_F = 820 \text{ A}$	$T_{vj} = 175^{\circ}\text{C}$	–	1.50	–	
			$T_{vj} = 25^{\circ}\text{C}$	–	1.70	–	
			$T_{vj} = 150^{\circ}\text{C}$	–	1.70	–	
			$T_{vj} = 175^{\circ}\text{C}$	–	1.65	–	
E_{rr}	Reverse Recovery Energy	$I_F = 600 \text{ A}$, $V_R = 400 \text{ V}$, $V_{GE} = -8 \text{ V}$, $R_{g,on} = 4 \Omega$					

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TYPICAL CHARACTERISTICS

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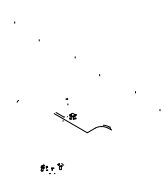
TYPICAL CHARACTERISTICS



VE-Trac™ Direct Module NVH820S75L4SPC

SSDC33, 154.50x92.0 (SPC)
CASE 183AC
ISSUE A

DATE 11 DEC 2019



**GENERIC
MARKING DIAGRAM***

XXXXXXXXXXXXXXXXXXXXXG ATYYWW

XXXXX = Specific Device Code
G = Pb-Free Package
AT = Assembly & Test Site Code
YYWW= Year and Work Week Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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